Jorge M Garcia

List of Publications by Year
in descending order

#	Article	IF	Citations
1	A successful exploitation of gamma-radiation on chalcogenide Cu2InSnS4 towards clean water under photocatalysis approach. Journal of Molecular Structure, 2022, 1251, 131943.	1.8	9
2	Synthesis of new promising quaternary Cu2InSnS4 absorber layer: Physical behaviors, wettability and photocatalysis applications. Journal of Alloys and Compounds, 2022, 898, 162771.	2.8	9
3	Exploration of spray pyrolysis technique in preparation of absorber material CFATS: Unprecedented hydrophilic surface and antibacterial properties. Arabian Journal of Chemistry, 2022, 15, 103894.	2.3	1
4	Competence of tunable Cu2AlSnS4 chalcogenides hydrophilicity toward high efficacy photodegradation of spiramycin antibiotic resistance-bacteria from wastewater under visible light irradiation. Journal of Photochemistry and Photobiology A: Chemistry, 2022, 431, 114041.	2.0	8
5	Growth of the next generation promising Cu2 Fe1-xCoxSnS4 thin films and efficient p-CCTS/n-In2S3/n-SnO2F heterojunction for optoelectronic applications. Materials Research Bulletin, 2021, 133, 111028.	2.7	12
6	A robust machine learning framework to identify signatures for frailty: a nested case-control study in four aging European cohorts. GeroScience, 2021, 43, 1317-1329.	2.1	31
7	Optimization of a carbon evaporator cell for MBE growth. Vacuum, 2020, 181, 109653.	1.6	0
8	First principal investigation of structural, morphological, optoelectronic and magnetic characteristics of sprayed Zn: Fe2O3 thin films. Optik, 2020, 219, 165303.	1.4	4
9	CFTS-3/In2S3/SnO2:F heterojunction structure as eco-friendly photocatalytic candidate for removing organic pollutants. Arabian Journal of Chemistry, 2020, 13, 6366-6378.	2.3	16
10	System for manufacturing complete Cu(In,Ga)Se2 solar cells in situ under vacuum. Solar Energy, 2020, 198, 490-498.	2.9	10
11	Production and processing of graphene and related materials. 2D Materials, 2020, 7, 022001.	2.0	333
12	Giant V oc Boost of Lowâ€Temperature Annealed Cu(In,Ga)Se 2 with Sputtered Zn(O,S) Buffers. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900145.	1.2	6
13	Physical properties investigation and gas sensing mechanism of Al: Fe2O3 thin films deposited by spray pyrolysis. Superlattices and Microstructures, 2019, 129, 91-104.	1.4	15
14	Circularly Polarized Emission from Ensembles of InGaAs/GaAs Quantum Rings. Silicon, 2017, 9, 689-693.	1.8	0
15	Exceptionally large migration length of carbon and topographically-facilitated self-limiting molecular beam epitaxial growth of graphene on hexagonal boron nitride. Carbon, 2017, 114, 579-584.	5.4	12
16	Epitaxial CuInSe2 thin films grown by molecular beam epitaxy and migration enhanced epitaxy. Journal of Crystal Growth, 2017, 475, 300-306.	0.7	10
17	Scanning tunneling spectroscopic monitoring of surface states role on water passivation of InGaAs uncapped quantum dots. RSC Advances, 2017, 7, 33137-33142.	1.7	0
18	Graphene growth on Pt(111) and Au(111) using a MBE carbon solid-source. Diamond and Related Materials, 2015, 57, 58-62.	1.8	27

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19	Magnetoplasmonic Nanorings as Novel Architectures with Tunable Magnetoâ€optical Activity in Wide Wavelength Ranges. Advanced Optical Materials, 2014, 2, 612-617.	3.6	27
20	Magnetoplasmonics: Magnetoplasmonic Nanorings as Novel Architectures with Tunable Magnetoâ€optical Activity in Wide Wavelength Ranges (Advanced Optical Materials 7/2014). Advanced Optical Materials, 2014, 2, 600-600.	3.6	0
21	Single- and bi-layer graphene grown on sapphire by molecular beam epitaxy. Solid State Communications, 2014, 189, 15-20.	0.9	13
22	0D Band Gap Engineering by MBE Quantum Rings: Fabrication and Optical Properties. Nanoscience and Technology, 2014, , 61-82.	1.5	1
23	Counting molecular-beam grown graphene layers. Applied Physics Letters, 2013, 102, 241905.	1.5	3
24	Molecular beam growth of graphene nanocrystals on dielectric substrates. Carbon, 2012, 50, 4822-4829.	5.4	34
25	Graphene growth on h-BN by molecular beam epitaxy. Solid State Communications, 2012, 152, 975-978.	0.9	92
26	Microcavity-Mediated Coupling of Two Distant InAsâˆ•GaAs Quantum Dots. , 2011, , .		0
27	Three dimensional atom probe imaging of GaAsSb quantum rings. Ultramicroscopy, 2011, 111, 1073-1076.	0.8	14
28	Multilayer graphene grown by precipitation upon cooling of nickel on diamond. Carbon, 2011, 49, 1006-1012.	5.4	56
29	Theoretical modelling of quaternary GaInAsSb/GaAs self-assembled quantum dots. Journal of Physics: Conference Series, 2010, 245, 012081.	0.3	4
30	Multilayer graphene films grown by molecular beam deposition. Solid State Communications, 2010, 150, 809-811.	0.9	35
31	Optical coupling of two distant InAs/GaAs quantum dots by a photonic-crystal microcavity. Physical Review B, 2010, 81, .	1.1	37
32	Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots. Physical Review B, 2010, 82, .	1.1	14
33	Publisher's Note: Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots [Phys. Rev. B82, 235316 (2010)]. Physical Review B, 2010, 82, .	1.1	0
34	Single photon emission and quantum ring-cavity coupling in InAs/GaAs quantum rings. Journal of Physics: Conference Series, 2010, 210, 012037.	0.3	1
35	Emission polarization control in semiconductor quantum dots coupled to a photonic crystal microcavity. Optics Express, 2010, 18, 13301.	1.7	17
36	Single-photon emission by semiconductor quantum rings in a photonic crystal. Journal of the Optical Society of America B: Optical Physics, 2010, 27, A21.	0.9	12

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37	Excitonic behavior in self-assembled InAs/GaAs quantum rings in high magnetic fields. Physical Review B, 2009, 80, .	1.1	33
38	Competition between carrier recombination and tunneling in quantum dots and rings under the action of electric fields. Superlattices and Microstructures, 2008, 43, 582-587.	1.4	3
39	Optical emission of InAs/GaAs quantum rings coupled to a two-dimensional photonic crystal microcavity. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2156-2159.	1.3	1
40	Temperature dependent optical properties of stacked InGaAs/GaAs quantum rings. Materials Science and Engineering C, 2008, 28, 887-890.	3.8	1
41	Carrier recombination effects in strain compensated quantum dot stacks embedded in solar cells. Applied Physics Letters, 2008, 93, 123114.	1.5	46
42	Isolated self-assembled InAs/InP(001) quantum wires obtained by controlling the growth front evolution. Nanotechnology, 2007, 18, 035604.	1.3	21
43	Enhancement of the room temperature luminescence of InAs quantum dots by GaSb capping. Applied Physics Letters, 2007, 91, .	1.5	31
44	Electro-Optical Characterization of Self-Assembled InAs/GaAs Quantum Rings Embedded in P-i-N and Schottky Diodes. AIP Conference Proceedings, 2007, , .	0.3	0
45	Oscillatory Persistent Currents in Self-Assembled Quantum Rings. Physical Review Letters, 2007, 99, 146808.	2.9	192
46	Manipulating exciton fine structure in quantum dots with a lateral electric field. Applied Physics Letters, 2007, 90, 041101.	1.5	186
47	Near Room Temperature InAs Quantum Wires Lasers on InP at Short Wavelength Infrared. , 2007, , .		0
48	Optical investigation of type II GaSbâˆ•GaAs self-assembled quantum dots. Applied Physics Letters, 2007, 91, .	1.5	86
49	Oscillatory persistent currents in nano-volcanoes. AIP Conference Proceedings, 2007, , .	0.3	0
50	(InP)5/(Ga0.47In0.53As)4 short-period superlattices waveguides for InAs quantum wires lasers. Journal of Crystal Growth, 2007, 306, 16-21.	0.7	0
51	Modulation spectroscopy on a single self assembled quantum dot. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 381-389.	0.8	2
52	Oscillator strength reduction induced by external electric fields in self-assembled quantum dots and rings. Physical Review B, 2007, 75, .	1.1	60
53	Effect of carrier transfer on the PL intensity in self-assembled In (Ga) As/GaAs quantum rings. EPJ Applied Physics, 2006, 35, 159-163.	0.3	10
54	Atomic-scale structure and formation of self-assembled In(Ga)As quantum rings. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 41-45.	1.3	27

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55	Magnetotunneling spectroscopy of ring-shaped (InGa)As quantum dots: Evidence of excited states with 2pz character. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 57-60.	1.3	0
56	Size filtering effect in vertical stacks of In(Ga)As/GaAs self-assembled quantum rings. Materials Science and Engineering C, 2006, 26, 297-299.	3.8	2
57	Enhancement of the photoluminescence intensity of a single InAs/GaAs quantum dot by separate generation of electrons and holes. Physics of the Solid State, 2006, 48, 1993-1999.	0.2	0
58	Lateral carrier tunnelling in stacked In(Ga)As/GaAs quantum rings. European Physical Journal B, 2006, 54, 217-223.	0.6	13
59	Shape dependent electronic structure and exciton dynamics in small In(Ga)As quantum dots. European Physical Journal B, 2006, 54, 471-477.	0.6	11
60	Self-assembled InAs quantum wire lasers on (001)InP at 1.6Î¼m. Applied Physics Letters, 2006, 89, 091123.	1.5	10
61	Strain determination in MBE-grownInAsquantum wires onInP. Physical Review B, 2006, 73, .	1.1	3
62	Ordered InAs quantum dots on pre-patterned GaAs (001) by local oxidation nanolithography. Journal of Crystal Growth, 2005, 284, 313-318.	0.7	36
63	Excited states of ring-shaped (InGa)As quantum dots in aGaAsâˆ•(AlGa)Asquantum well. Physical Review B, 2005, 72, .	1.1	13
64	Modeling of the Magnetization Behavior of Realistic Self-Organized InAs/GaAs Quantum Craters as Observed with Cross-Sectional STM. AIP Conference Proceedings, 2005, , .	0.3	5
65	Continuum and discrete excitation spectrum of single quantum rings. Physical Review B, 2005, 72, .	1.1	47
66	Room temperature emission at 1.6Î¼m from InGaAs quantum dots capped with GaAsSb. Applied Physics Letters, 2005, 87, 202108.	1.5	106
67	Absorption and photoluminescence spectroscopy on a single self-assembled charge-tunable quantum dot. Physical Review B, 2005, 72, .	1.1	65
68	Determination of the energy levels on InAs quantum dots with respect to the GaAs conduction band. Nanotechnology, 2005, 16, S282-S284.	1.3	15
69	Atomic-scale structure of self-assembled In(Ga)As quantum rings in GaAs. Applied Physics Letters, 2005, 87, 131902.	1.5	126
70	Vertical order in stacked layers of self-assembled In(Ga)As quantum rings on GaAs (001). Applied Physics Letters, 2005, 86, 071918.	1.5	71
71	Hybridization of electronic states in quantum dots through photon emission. Nature, 2004, 427, 135-138.	13.7	113
72	Confinement in self-assembled InAs/InP quantum wires studied by magneto-photoluminescence. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 261-264.	1.3	3

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73	In segregation effects during quantum dot and quantum ring formation on GaAs(001). Microelectronics Journal, 2004, 35, 7-11.	1.1	15
74	Stress evolution aspects during InAs/InP (001) quantum wires self-assembling. Microelectronics Journal, 2004, 35, 13-17.	1.1	21
75	Fine structure of highly charged quantum dot excitons: turning dark into bright states. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 421-425.	0.8	0
76	Temperature study of the photoluminescence of a single InAs/GaAs quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 608-611.	0.8	0
77	Electronic quantum dot states induced through photon emission. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2079-2093.	0.8	0
78	Emission from neutral and charged excitons in a single quantum dot in a magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 184-188.	1.3	10
79	Magneto-excitonic states in charge-tunable self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 25, 233-241.	1.3	4
80	Temperature-dependent linewidth of charged excitons in semiconductor quantum dots: Strongly broadened ground state transitions due to acoustic phonon scattering. Physical Review B, 2004, 69, .	1.1	47
81	Laser devices with stacked layers of InGaAs/GaAs quantum rings. Nanotechnology, 2004, 15, S126-S130.	1.3	71
82	Electron wave-function spillover in self-assembledInAsâˆ•InPquantum wires. Physical Review B, 2004, 70, .	1.1	44
83	Effective tuning of the charge-state of single In(Ga)As/GaAs quantum dots by below barrier band gap excitation. Surface Science, 2003, 532-535, 843-847.	0.8	0
84	Grazing incidence diffraction anomalous fine structure of self-assembled semiconductor nanostructures. Nuclear Instruments & Methods in Physics Research B, 2003, 200, 24-33.	0.6	3
85	Controlling the shape of InAs self-assembled quantum dots by thin GaAs capping layers. Journal of Crystal Growth, 2003, 251, 155-160.	0.7	32
86	Customized nanostructures MBE growth: from quantum dots to quantum rings. Journal of Crystal Growth, 2003, 251, 213-217.	0.7	17
87	Glancing angle EXAFS of encapsulated self-assembled InAs/InP quantum wires and InAs/GaAs quantum dots. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 174-180.	1.7	8
88	Charged excitons in individual quantum dots: effects of vertical electric fields and optical pump power. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 35-36.	1.3	7
89	Vertical stacks of small InAs/GaAs self-assembled dots: resonant and non-resonant excitation. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 46-49.	1.3	8
90	Size self-filtering effect in vertical stacks of InAs/InP self-assembled quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 174-176.	1.3	3

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91	Grazing incidence diffraction anomalous fine structure: a tool for investigating strain distribution and interdiffusion in InAs/InP quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 541-542.	1.3	3
92	Magnetic properties of charged excitons in self-assembled quantum dots. Physica Status Solidi (B): Basic Research, 2003, 238, 293-296.	0.7	4
93	In(Ga)As self-assembled quantum ring formation by molecular beam epitaxy. Applied Physics Letters, 2003, 82, 2401-2403.	1.5	195
94	Effect of an additional infrared excitation on the luminescence efficiency of a single InAs/GaAs quantum dot. Physical Review B, 2003, 68, .	1.1	37
95	Fine Structure of Highly Charged Excitons in Semiconductor Quantum Dots. Physical Review Letters, 2003, 90, 247403.	2.9	124
96	Scanning tunnelling microscopy and spectroscopy on organic PTCDA films deposited on sulfur passivated GaAs(001). Journal of Physics Condensed Matter, 2003, 15, S2619-S2629.	0.7	24
97	Acceptor-induced threshold energy for the optical charging of InAs single quantum dots. Physical Review B, 2002, 66, .	1.1	24
98	Magneto-optical properties of charged excitons in quantum dots. Physical Review B, 2002, 66, .	1.1	63
99	Preparation and passivation of GaAs(001) surfaces for growing organic molecules. Nanotechnology, 2002, 13, 352-356.	1.3	10
100	Grazing-incidence diffraction anomalous fine structure of InAs/InP(001) self-assembled quantum wires. Europhysics Letters, 2002, 57, 499-505.	0.7	28
101	Charged Excitons in Self-assembled Quantum Dots. Materials Research Society Symposia Proceedings, 2002, 737, 75.	0.1	1
102	Optical Charging of Self-Assembled InAs/GaAs Quantum Dots. Physica Scripta, 2002, T101, 140.	1.2	0
103	Influence of the InAs coverage on the phonon-assisted recombination in InAs/GaAs quantum dots. Surface Science, 2002, 507-510, 624-629.	0.8	1
104	Formation of the charged exciton complexes in self-assembled InAs single quantum dots. Journal of Applied Physics, 2002, 92, 6787-6793.	1.1	19
105	Giant permanent dipole moments of excitons in semiconductor nanostructures. Physical Review B, 2002, 65, .	1.1	147
106	Size-filtering effects by stacking InAs/InP (001) self-assembled quantum wires into multilayers. Physical Review B, 2002, 65, .	1.1	25
107	Carrier Recombination in InAs/GaAs Self-Assembled Quantum Dots under Resonant Excitation Conditions. Physica Status Solidi A, 2002, 190, 583-587.	1.7	2
108	Exciton Recombination in Self-Assembled InAs/GaAs Small Quantum Dots under an External Electric Field. Physica Status Solidi A, 2002, 190, 599-603.	1.7	2

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109	Optical Properties of Self-Assembled GaxIn1-xAs/InP Quantum Wires. Physica Status Solidi A, 2002, 190, 763-768.	1.7	3
110	Morphological transformation of InyGa1â^'yAs islands, fabricated by Stranskiâ€"Krastanov growth. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 225-229.	1.7	52
111	The influence of carrier diffusion on the formation of charged excitons in InAs/GaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 101-104.	1.3	2
112	Magneto-optical properties of ring-shaped self-assembled InGaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 165-169.	1.3	45
113	Limited In incorporation during pseudomorphic InAs/GaAs growth and quantum dot formation observed by in situ stress measurements. Applied Surface Science, 2002, 188, 75-79.	3.1	9
114	In situ measurements of As/P exchange during InAs/InP(0 0 1) quantum wires growth. Applied Surface Science, 2002, 188, 188-192.	3.1	20
115	Temperature influence on optical charging of self-assembled InAs/GaAs semiconductor quantum dots. Applied Physics Letters, 2001, 78, 2952-2954.	1.5	32
116	Epitaxial metallic nanostructures on GaAs. Surface Science, 2001, 482-485, 910-915.	0.8	11
117	Luminescence quenching in InAs quantum dots. Applied Physics Letters, 2001, 78, 2946-2948.	1.5	39
118	Glancing-angle diffraction anomalous fine structure of InAs quantum dots and quantum wires. Journal of Synchrotron Radiation, 2001, 8, 536-538.	1.0	8
119	Optical emission from single, charge-tunable quantum rings. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 9, 124-130.	1.3	27
120	A growth method to obtain flat and relaxed In0.2Ga0.8As on GaAs (001) developed through in situ monitoring of surface topography and stress evolution. Journal of Crystal Growth, 2001, 227-228, 36-40.	0.7	1
121	InAs/InP(001) quantum wire formation due to anisotropic stress relaxation: in situ stress measurements. Journal of Crystal Growth, 2001, 227-228, 975-979.	0.7	77
122	Surface stress effects during MBE growth of IIIâ€"V semiconductor nanostructures. Journal of Crystal Growth, 2001, 227-228, 995-999.	0.7	20
123	Optical Up-Conversion Processes in InAs Quantum Dots. Japanese Journal of Applied Physics, 2001, 40, 2080-2083.	0.8	8
124	Growth and Electronic Properties of Self-Organized Quantum Rings. Japanese Journal of Applied Physics, 2001, 40, 1857-1859.	0.8	74
125	Excited-State Magnetoluminescence of InAs/GaAs Self-Assembled Quantum Dots. Japanese Journal of Applied Physics, 2001, 40, 1998-2001.	0.8	0
126	Influence of excitation energy on charged exciton formation in self-assembled InAs single quantum dots. Physical Review B, 2001, 64, .	1.1	33

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127	Optical transitions and excitonic recombination in InAs/InP self-assembled quantum wires. Applied Physics Letters, 2001, 78, 4025-4027.	1.5	65
128	Carrier Diffusion in the Barrier Enabling Formation of Charged Excitons in InAs/GaAs Quantum Dots. Acta Physica Polonica A, 2001, 100, 387-395.	0.2	2
129	Excitons in self-assembled quantum ring-like structures. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 510-513.	1.3	82
130	Auger processes in InAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 440-443.	1.3	15
131	Optical emission from a charge-tunable quantum ring. Nature, 2000, 405, 926-929.	13.7	832
132	Strain-induced optical anisotropy in self-organized quantum structures at the E1 transition. Applied Physics Letters, 2000, 76, 2197-2199.	1.5	14
133	Magnetoluminescence of highly excited InAs/GaAs self-assembled quantum dots. Physical Review B, 2000, 62, 7344-7349.	1.1	30
134	Critical size for localization of the L-like conduction states in InAs quantum dots grown on GaAs. Applied Physics Letters, 2000, 76, 2919-2921.	1.5	0
135	Strain relaxation and segregation effects during self-assembled InAs quantum dots formation on GaAs(001). Applied Physics Letters, 2000, 77, 409-411.	1.5	99
136	Spectroscopy of Nanoscopic Semiconductor Rings. Physical Review Letters, 2000, 84, 2223-2226.	2.9	765
137	Influence of buffer-layer surface morphology on the self-organized growth of InAs on InP(001) nanostructures. Applied Physics Letters, 2000, 76, 1104-1106.	1.5	133
138	Nanometer-Scale Resolution of Strain and Interdiffusion in Self-AssembledInAs/GaAsQuantum Dots. Physical Review Letters, 2000, 85, 1694-1697.	2.9	203
139	Optical Properties of Semiconductor Nanostructures. , 2000, , .		13
140	Carrier-carrier correlations in an optically excited single semiconductor quantum dot. Physical Review B, 2000, 61, 11009-11020.	1.1	117
141	Photoluminescence up-conversion in InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2000, 77, 812-814.	1.5	91
142	Interband Optics of Charge-Tunable Quantum Dots. , 2000, , 347-363.		0
143	Interdependence of strain and shape in self-assembled coherent InAs islands on GaAs. Europhysics Letters, 1999, 45, 222-227.	0.7	44
144	Electronic structure of nanometer-size quantum dots and quantum rings. Microelectronic Engineering, 1999, 47, 95-99.	1.1	24

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145	Surface characterization of IIIâ€“V heteroepitaxial systems by laser light scattering. Journal of Crystal Growth, 1999, 201-202, 137-140.	0.7	4
146	Fe thin-film growth on Au(100): A self-surfactant effect and its limitations. Physical Review B, 1999, 59, 15966-15974.	1.1	58
147	Optical Spectroscopy of Single Self Assembled Quantum Dots. Materials Research Society Symposia Proceedings, 1999, 571, 135.	0.1	0
148	Tuning of electronic states in self-assembled InAs quantum dots using an ion implantation technique. Journal of Electronic Materials, 1998, 27, 1030-1033.	1.0	17
149	Field dependent carrier dynamics and charged excitons in InAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 627-631.	1.3	7
150	Optical spectroscopy of a single self-assembled quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 694-700.	1.3	3
151	Giant magnetoresistance in a low-temperature GaAs/MnAs nanoscale ferromagnet hybrid structure. Applied Physics Letters, 1998, 73, 3291-3293.	1.5	57
152	Electronic states tuning of InAs self-assembled quantum dots. Applied Physics Letters, 1998, 72, 3172-3174.	1.5	149
153	Intersublevel transitions in InAs/GaAs quantum dots infrared photodetectors. Applied Physics Letters, 1998, 73, 2003-2005.	1.5	254
154	Multiexciton Spectroscopy of a Single Self-Assembled Quantum Dot. Physical Review Letters, 1998, 80, 4991-4994.	2.9	329
155	Strain and Shape in Self-Assembled Quantum Dots Studied by X-Ray Grazing Incidence Diffraction. Materials Research Society Symposia Proceedings, 1998, 524, 89.	0.1	0
156	Formation and Properties of Nanosize Ferromagnetic MnAs Particles in Low Temperature GaAs by Manganese Implantation. Materials Research Society Symposia Proceedings, 1997, 475, 49.	0.1	0
157	Charging dynamics of InAs self-assembled quantum dots. Physical Review B, 1997, 56, 3609-3612.	1.1	43
158	Size quantization effects in InAs self-assembled quantum dots. Applied Physics Letters, 1997, 70, 1727-1729.	1.5	82
159	Formation of nanoscale ferromagnetic MnAs crystallites in low-temperature grown GaAs. Applied Physics Letters, 1997, 71, 2532-2534.	1.5	104
160	Intermixing and shape changes during the formation of InAs self-assembled quantum dots. Applied Physics Letters, 1997, 71, 2014-2016.	1.5	559
161	Straindashinduced enhanced solubility of Au in epitaxial films of Fe. Surface Science, 1996, 364, L505-L510.	0.8	11
162	Lateral confinement of surface states on stepped Cu(111). Physical Review B, 1995, 52, 7894-7897.	1.1	73

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163	Confining surface state electrons in less than two dimensions: A spectroscopic study. Applied Physics A: Materials Science and Processing, 1995, 61, 609-613.	1.1	3
164	A structural characterization of the buffer layer for growth of magnetically coupled Co/Cu superlattices. Journal of Magnetism and Magnetic Materials, 1993, 121, 20-23.	1.0	1
165	Metallization-induced spontaneous silicide formation at room temperature: The Fe/Si case. Physical Review B, 1992, 46, 13339-13344.	1.1	90
166	Growth of epitaxial iron disilicide on Si(100). Surface Science, 1992, 269-270, 1016-1021.	0.8	13
167	Pure luminescence transitions from a small InAs/GaAs quantum dot exhibiting a single electron level. , 0, , .		0
168	Luminescence and photocurrent spectroscopy of self-assembled InAs quantum wires on InP[001]. , 0, , .		0
169	Chemical composition and strain distribution of InAs/GaAs(001) stacked quantum rings. , 0, , 271-274.		0